

Amendments to the Claims:

1. **(Original)** A semiconductor wafer treatment member having at least a surface formed with a silicon carbide (SiC) film thereon, comprising a support portion for supporting a semiconductor wafer, said support portion being composed of salients with which said semiconductor wafer substantially comes into contact; and depressions formed with the silicon carbide (SiC) film to provide a coverage area between said salients, said salients being formed with upper faces having a surface roughness Ra of 0.05 μ m to 1.3 μ m.
2. **(Original)** A semiconductor wafer treatment member as set forth in claim 1, wherein said coverage area has a ratio of 20 to 90 % to a total area of said depressions.
3. **(Currently amended)** A semiconductor wafer treatment member as set forth in claim 1 ~~or claim 2~~, wherein said depressions have faces having a surface roughness Ra of 3 μ m or more when measured for a length of 300 μ m.
4. **(Currently amended)** A semiconductor wafer treatment member as set forth in claim 1 ~~or 2~~, wherein said top surfaces of the salients and said surfaces of the depression have boundary portions in the form of curves.
5. **(Original)** A semiconductor wafer treatment member as set forth in claim 3, wherein said boundary portions connecting said top surfaces of the salients and said faces of the depressions in the form of curves.
6. **(New)** A semiconductor wafer treatment member as set forth in claim 2, wherein said depressions have faces having a surface roughness Ra of 3 μ m or more when measured for a length of 300 μ m.

7. **(New)** A semiconductor wafer treatment member as set forth in claim 2, wherein said top surfaces of the salients and said surfaces of the depression have boundary portions in the form of curves.